

# FDG313N

# **Digital FET, N-Channel**

### **General Description**

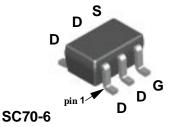
This N-Channel enhancement mode field effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistor and small signal MOSFET.

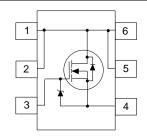
### **Applications**

- Load switch
- Battery protection
- Power management

#### **Features**

- 0.95 A, 25 V.  $R_{DS(on)} = 0.45~\Omega$  @  $V_{GS} = 4.5~V$   $R_{DS(on)} = 0.60~\Omega$  @  $V_{GS} = 2.7~V$ .
- Low gate charge (1.64 nC typical)
- Very low level gate drive requirements allowing direct operation in 3V circuits (V<sub>GS(th)</sub> < 1.5V).</li>
- Gate-Source Zener for ESD ruggedness (>6kV Human Body Model).
- Compact industry standard SC70-6 surface mount package.





Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDG313N	Units	
V <sub>DSS</sub>	Drain-Source Voltage	25	V	
V <sub>GSS</sub>	Gate-Source Voltage		<u>+</u> 8	V
I <sub>D</sub>	Drain Current - Continuous	0.95	Α	
	- Pulsed		2	
$P_D$	Power Dissipation for Single Operation	(Note 1a)	0.75	W
		(Note 1b)	0.55	
		(Note 1c)	0.48	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperatu	re Range	-55 to +150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883 Human Body Model (100pf / 1500 Ohm)	3D	6	kV

## **Thermal Characteristics**

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R <sub>AJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1c)	260	°C/W						

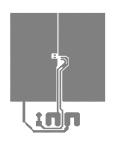
**Package Outlines and Ordering Information** 

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_	Device Marking	Device	Reel Size	Tape Width	Quantity	
	.13	FDG313N	7"	8mm	3000 units	_

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250  \mu\text{A}$	25			V
<u>Δ</u> BVdss ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		30		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSS</sub>	Gate-Body Leakage Current	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250  \mu A$	0.65	0.8	1.5	V
<u>Δ</u> VGS(th) ΔΤ <sub>J</sub>	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		-2		mV/∘C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 0.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 0.5 \text{ A}$ @ 125°C $V_{GS} = 2.7 \text{ V}, I_D = 0.2 \text{ A}$		0.35 0.53 0.45	0.45 0.76 0.6	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	0.5			Α
<b>g</b> fs	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 0.5 \text{ A}$		1.5		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		50		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		28		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	7		9		pF
Switchin	g Characteristics (Note 2)		I	ı	1	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 6 \text{ V}, I_D = 0.5 \text{ A},$		3	6	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 50 \Omega$		8.5	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1		17	30	ns
t <sub>f</sub>	Turn-Off Fall Time	7		13	25	ns
$Q_g$	Total Gate Charge	$V_{DS} = 5 \text{ V}, I_{D} = 0.95 \text{ A},$		1.64	2.3	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		0.38		nC
$Q_{gd}$	Gate-Drain Charge	7		0.45		nC
Drain-So	ource Diode Characteristics a	nd Maximum Ratings	•	•	•	
<u> סומווו-טט</u> I <sub>s</sub>	Maximum Continuous Drain-Source I				0.6	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 0.6 \text{ A} \text{ (Note 2)}$	<del>                                     </del>	0.8	1.2	V

#### Notes

 R<sub>B,JA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>B,JC</sub> is guaranteed by design while R<sub>B,JA</sub> is determined by the user's board design.



a) 170°C/W when mounted on a 1 in² pad of 2oz copper.



b) 225°C/W when mounted on a half of package sized 2oz. copper.



c) 260°C/W when mounted on a minimum pad of 2oz copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq 300~\mu s$ , Duty Cycle  $\leq 2.0\%$ 

# **Typical Characteristics**

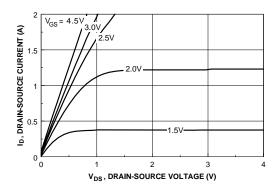


Figure 1. On-Region Characteristics.

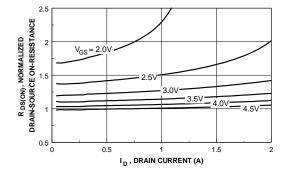


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

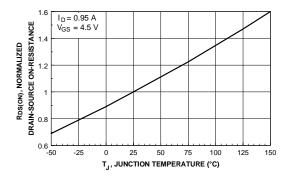


Figure 3. On-Resistance Variation with Temperature.

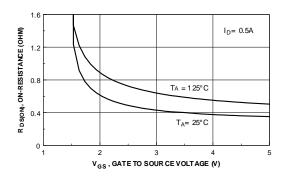


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

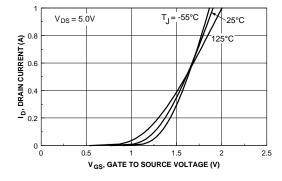


Figure 5. Transfer Characteristics.

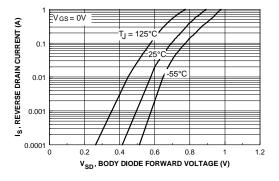
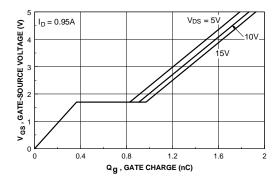


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# Typical Characteristics (continued)



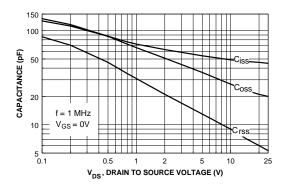
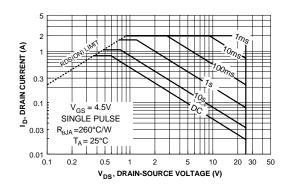


Figure 7. Gate-Charge Characteristics.





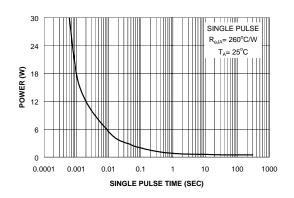


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

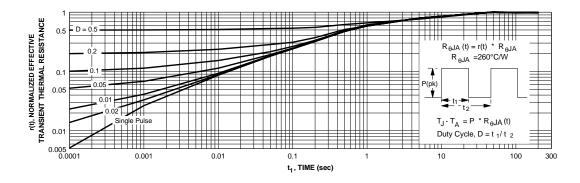
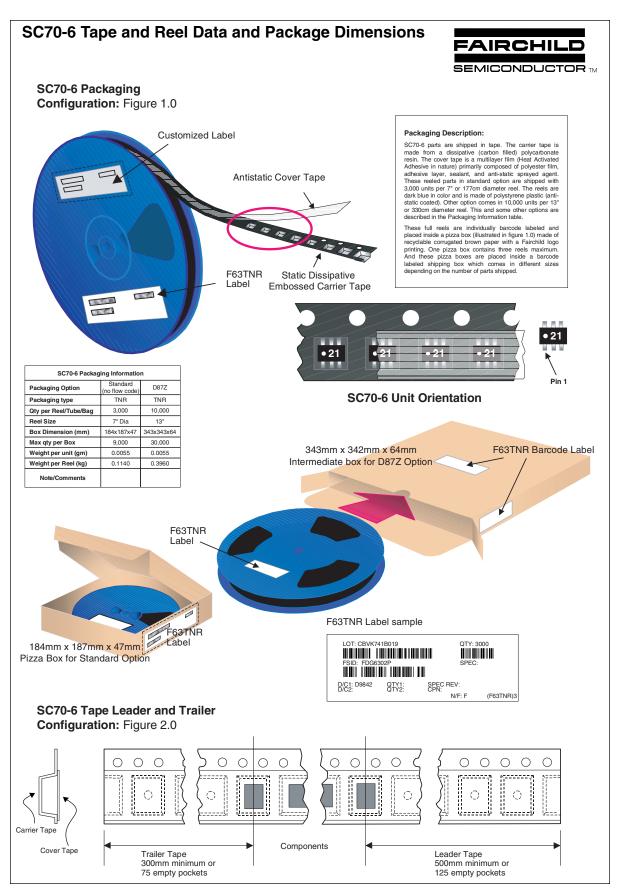


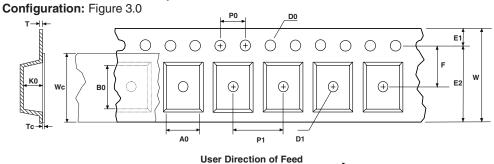
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.





# **SC70-6 Embossed Carrier Tape**

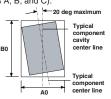


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SC70-6 (8mm)	2.24 +/-0.10	2.34 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.20 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

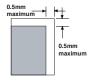
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



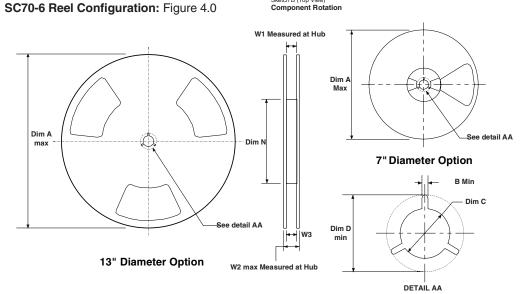
Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement



Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SC70-6 Tape and Reel Data and Package Dimensions, continued SC70-6 (FS PKG Code 76) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.0055 2.00±0.20-0.65 -0.50 MIN 1.25±0.10 1.90 $\mathbb{H}$ (0.25)0.40 MIN **♦** 0.10**M** A B 0.65 LAND PATTERN RECOMMENDATION 1.30 SEE DETAIL A 0.10 0.10 0 卣 -(0.43)SEATING -2.10±0,30-PLANE GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED (R0.10) THIS PACKAGE CONFORMS TO EIAJ SC-8B, 1996. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. 0.20 DETAIL A MAAO&AREVD

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